

TI 918L-600-25

Integrated Gate-Commutated Thyristor

Properties

- Full reverse voltage
- Low on-state losses
- Snubberless
- Suitable for inverters, drives and traction applications
- High reliability

Key Parameters

V_{DRM}, V_{RRM}	=	2 500	V
I_{TGQM}	=	600	A
I_{TAVm}	=	630	A
I_{TSM}	=	10 000	A
V_{TO}	=	1.495	V
r_T	=	1.37	mΩ

Types

	V_{DRM}, V_{RRM}
TI 918L-600-30	3 000 V
TI 918L-600-25	2 500 V
TI 918L-600-20	2 000 V

Mechanical Data (see Fig. 6)

F_m	Mounting force	10 ± 2 kN
m	Weight	0.890 kg
D_s	Surface creepage distance	25 mm
D_a	Air strike distance	12 mm
D_p	Pole-piece diameter	47 mm
l	Length	230 mm
h	Height	57 mm
w	Width	112 mm



Fig. 1 Case

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Maximum Ratings			Maximum Limits	Unit
V_{DRM} V_{RRM}	Repetitive peak off-state and peak reverse voltage $T_j = -40 \div 115 \text{ }^\circ\text{C}$, Gate unit energized	TI 918L-600-30 TI 918L-600-25 TI 918L-600-20	3 000 2 500 2 000	V
V_{Dclink}	Permanent DC voltage for $\lambda = 100$ FIT failure rate Gate unit energized	TI 918L-600-30 TI 918L-600-25 TI 918L-600-20	1 800 1 500 1 200	V
I_{TRMS}	RMS on-state current $T_c = 70 \text{ }^\circ\text{C}$, half sine waveform, $f = 50 \text{ Hz}$		990	A
I_{TAVm}	Average on-state current $T_c = 70 \text{ }^\circ\text{C}$, half sine waveform, $f = 50 \text{ Hz}$		630	A
I_{TSM}	Peak non-repetitive surge half sine pulse, $t_p = 10 \text{ ms}$, $V_R = 0 \text{ V}$		10 000	A
I^2t	Limiting load integral half sine pulse, $t_p = 10 \text{ ms}$, $V_R = 0 \text{ V}$		500 000	A ² s
$T_{jmin} - T_{jmax}$	Junction operating temperature range		-40 \div 115	$^\circ\text{C}$
$T_{stgmin} - T_{stgmax}$	Storage temperature range		-40 \div 80	$^\circ\text{C}$

Unless otherwise specified $T_j = 115 \text{ }^\circ\text{C}$

Characteristics		Value			Unit
		min.	typ.	max.	
V_{TM}	Maximum peak on-state voltage $I_{TM} = 600 \text{ A}$, CS - ON			2.31	V
V_{T0}	Threshold voltage			1.495	V
r_T	Slope resistance $I_{T1} = 333 \text{ A}$, $I_{T2} = 1000 \text{ A}$			1.37	mΩ
I_{DM}	Peak off-state current $V_D = V_{DRM}$, Gate unit energized			150	mA
I_{RM}	Peak reverse current $V_R = V_{RRM}$, Gate unit energized			150	mA

Unless otherwise specified $T_j = 115 \text{ °C}$

Turn-on switching

Maximum rated values		Value	Unit
$(di_T/dt)_{cr}$	Critical rate of rise of on-state current	800	A/μs
Conditions: $T_j = 90 \text{ °C}$, $I_T = 600 \text{ A}$, $f = 0 \div 1000 \text{ Hz}$			
Characteristic values		Value	Unit
I_{Tm}	Peak on-state current	600	A
t_{don}	Turn-on delay time	≤ 2.5	μs
t_r	Rise on-time	≤ 0.7	μs
E_{on}	Turn-on energy per pulse	≤ 0.2	J
Conditions: $T_j = 90 \text{ °C}$, $L_{CL} = 0.2 \mu\text{H}$, $L_i = 2 \mu\text{H}$, $R_s = 12 \text{ } \Omega$, $V_{LC} = 0.6 V_{DRM}$. (Fig. 8)			

Turn-off switching

Maximum rated values		Value	Unit
I_{TGQM}	Max. controllable turn-off current	600	A
t_{doff}	Turn-off delay time	≤ 3.5	μs
t_f	Fall time	≤ 0.5	μs
E_{off}	Turn-off energy per pulse	≤ 1.0	J
Conditions: $T_j = 90 \text{ °C}$, $C_{CL} = 2 \text{ } \mu\text{F}$, $L_{CL} = 0.2 \mu\text{H}$, $L_i = 2 \mu\text{H}$, $R_s = 12 \text{ } \Omega$, $V_{LC} = 0.6 V_{DRM}$. (Fig. 8)			

Thermal Parameters		Value	Unit
R_{thjc}	Thermal resistance junction to case <i>double side cooling</i>	24.0	K/kW
R_{thch}	Thermal resistance case to heatsink, <i>double side cooling</i>	6.0	K/kW

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Polovodice, a.s. reserves the right to change the data contained herein at any time without notice

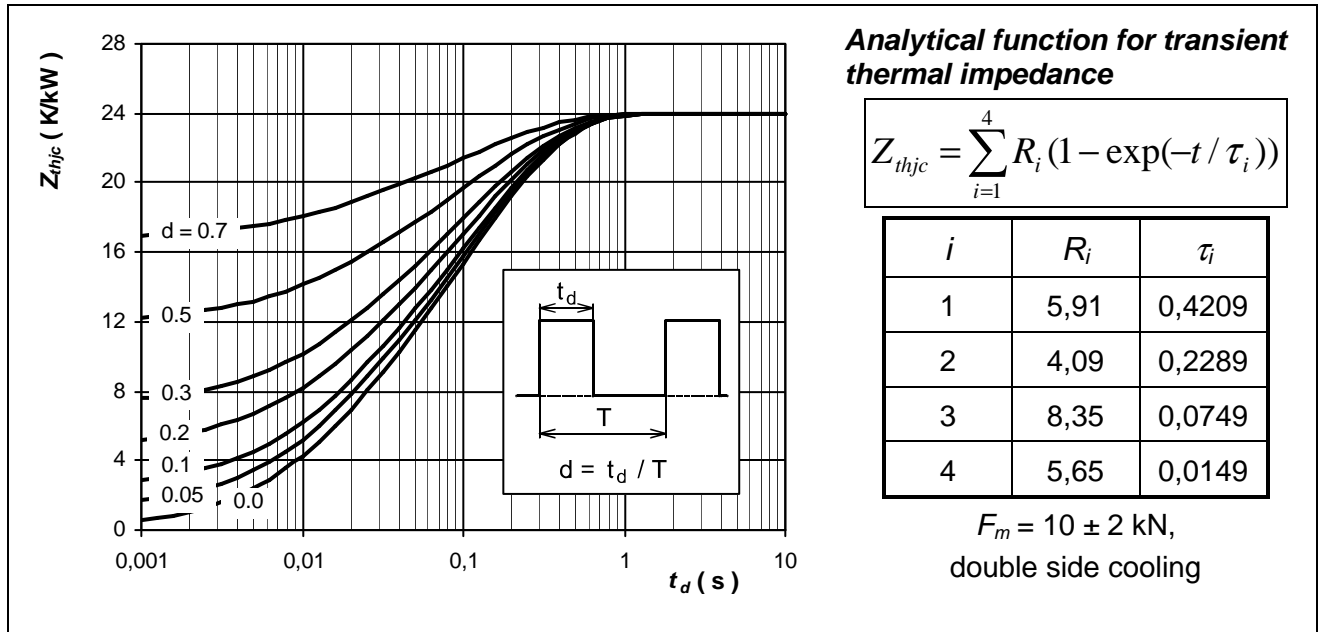


Fig.2 Transient thermal impedance junction to case

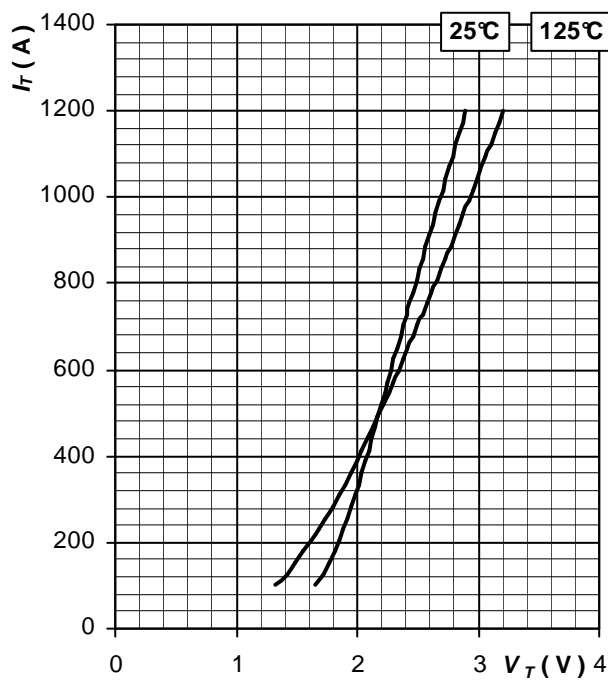


Fig.3 Maximum instantaneous on-state characteristics

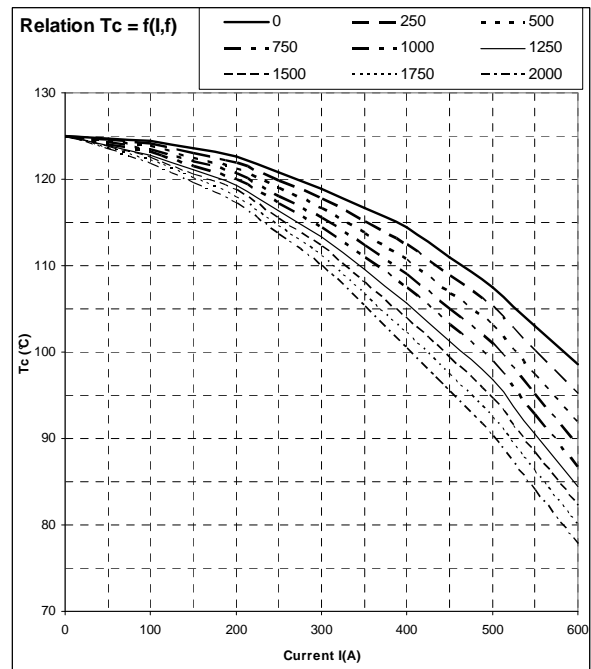


Fig.4 Maximum allowable case temperature T_c on rectangular turn-off current and frequency. Conditions: $C_{CL} = 3 \mu F$, $L_{CL} = 0.2 \mu H$, $L_i = 3 \mu H$, $R_s = 12 \Omega$, $V_D = 1500 V$

Gate unit		Value	Unit
V_{GIN1}	Gate unit voltage	- 20	V
V_{GIN2}	Input turn-on voltage	2.5	V
P_{max}	Gate unit power consumption ¹⁾	80	W
$P_{on CS}$	Control Signal optical input power (B1)	> -20	dBm
$P_{off CS}$	Control Signal optical noise power (B1)	< -45	dBm
$P_{on SF}$	Status Feedback optical output power(B2)	> -20	dBm
$P_{off SF}$	Status Feedback optical noise power (B2)	< -50	dBm
t_{onmin}	Minimal on time	$5 \pm 20\%$	μs
t_{offmin}	Minimal off time	$6 \pm 20\%$	μs
t_{GLITCH}	Pulse width threshold	< 0.75	μs
f_{max}	Frequency	2 000	Hz
t_{fd}	Delay time of on gate current	2.0	μs
t_{rd}	Delay time of off gate current	2.0	μs
D_{max}	Maximum duty	100	%
$T_{wmin} - T_{wmax}$	Operating temperature range ²⁾ (Fig. 5)	-20 ÷ 70	°C
$T_{stgmin} - T_{stgmax}$	Storage temperature range	-40 ÷ 80	°C
X1	Gate part power connector (see Fig.6)	BU0403 Hartman	-
CS - B1	LWL receiver for command signal	HFBR-2524 Agilent	-
SF - B2	LWL transmitter for status feedback	HFBR-1528 Agilent	-

Note 1: Powered with recommended supply unit SU 918A

Note 2: Recommended temperature: $\leq 60^{\circ}C$

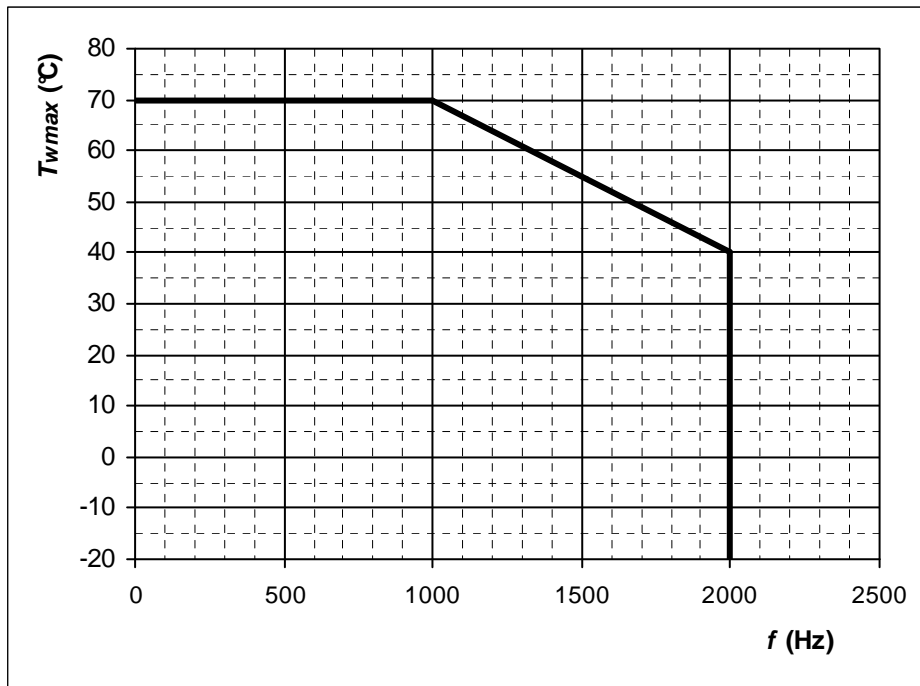


Fig. 5 Gate drive part operating temperature area

Supply unit (recommended type)		Value	Unit
V _c	DC power supply – SU 918A - SU 918A-48	18 ÷ 36 36 ÷ 60	V
P	Power consumption (cut-off limit)	90	W
V _{out1}	Output supply voltage	-20	V
T _{wmin} - T _{wmax}	Operating temperature range ²⁾	-20 to +70	°C
V _{is/1min}	Insulation strength	5.0	[kV]
m	Weight	1 220	g

Note 2: Recommended temperature: ≤ 60°C

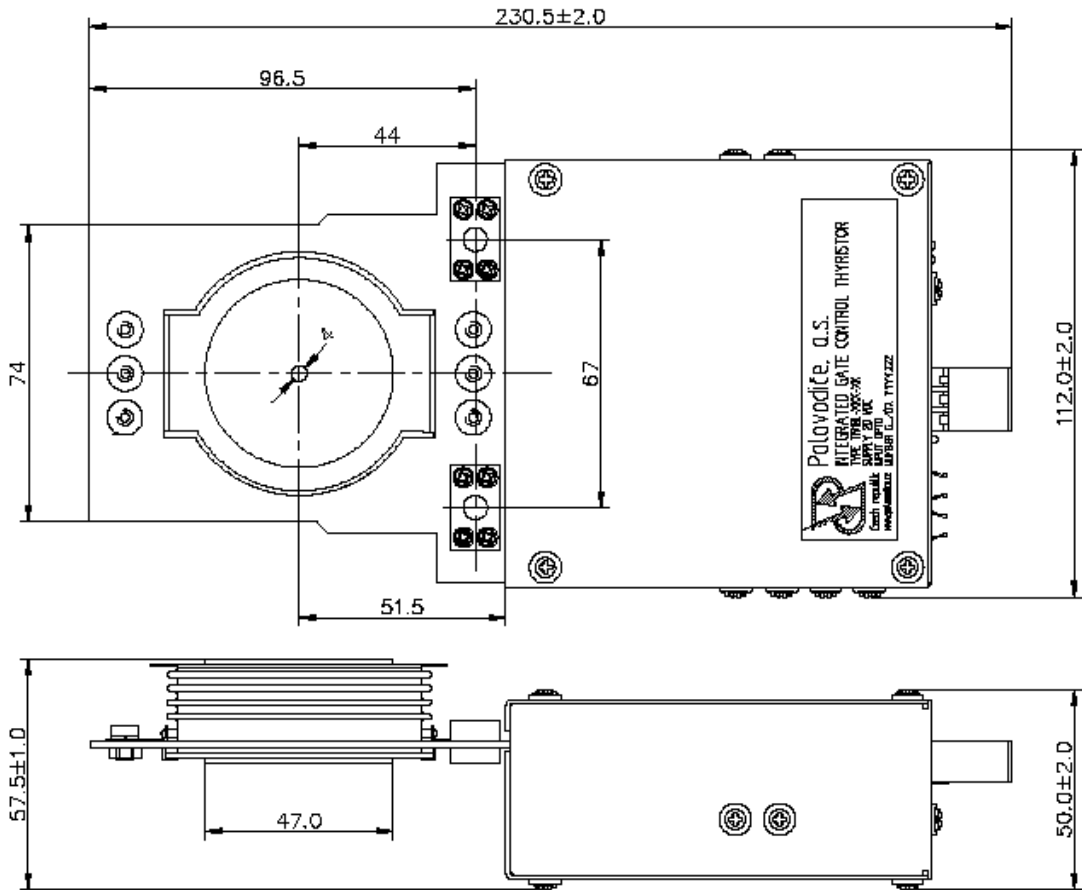


Fig. 6 Device gate part drawing

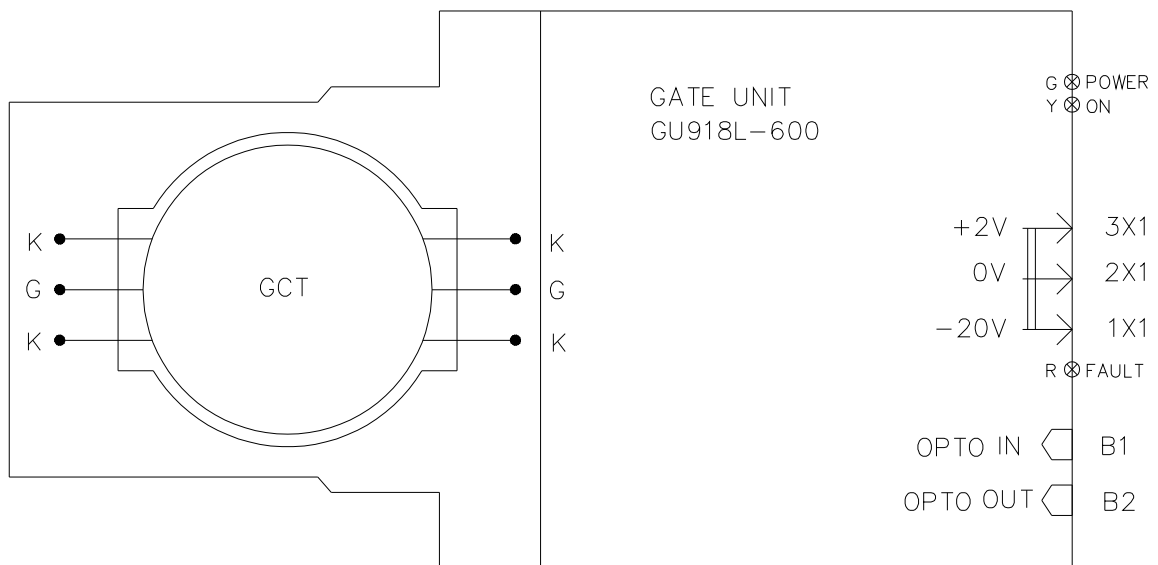


Fig. 7 Schema of input-output connection

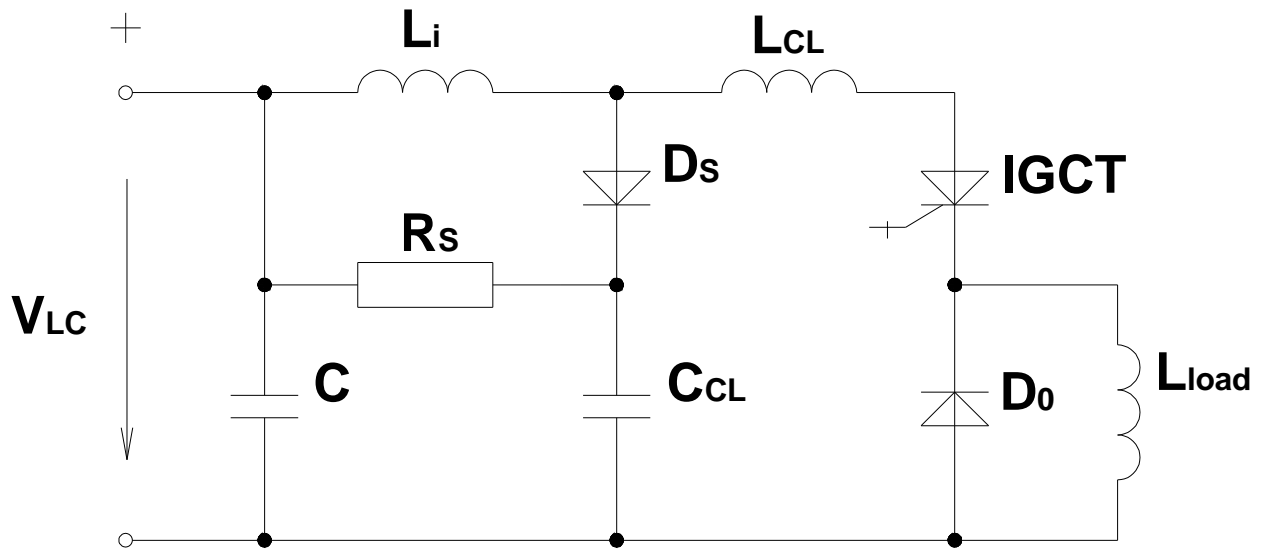


Fig.8 Test circuit.

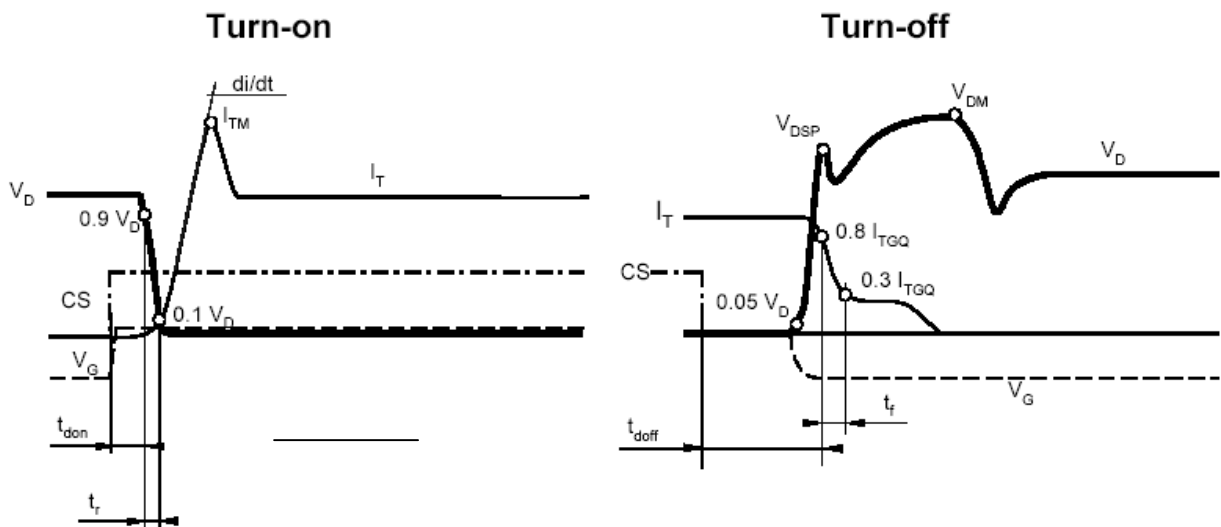


Fig. 9 Turn-on and turn-off waveform diagram